SN74LV138A-Q1 車載 3 ライン対 8 ライン・デコーダ / デマルチプレクサ

1 特長

- 車載アプリケーション用に AEC-Q100 認定済み:
  - デバイス温度グレード 1:-40℃～+125℃、T_A
  - デバイス HBM ESD 分類レベル 2
  - デバイス CDM ESD 分類レベル C6
- 2V～5.5V の V_{CC} で動作
- 最大 t_{pd} 9.5ns (5V 時)
- 標準 V_{OLP} (出力グランド・バウンス) < 0.8V (V_{CC} = 3.3V、T_A = 25℃)
- 標準 V_{OHV} (出力 V_{OH} アンダーシュート) > 2.3V (V_{CC} = 3.3V、T_A = 25℃)
- すべてのポートで混在モード電圧動作をサポート
- I_{off} により部分的パワーダウン・モードでの動作をサポート
- JESD 17 準拠で 250mA 超のラッチアップ性能

2 アプリケーション

- 出力拡張
- LED マトリクス制御
- 7 セグメント・ディスプレイ制御
- 8 ビット・データ・ストレージ

3 概要

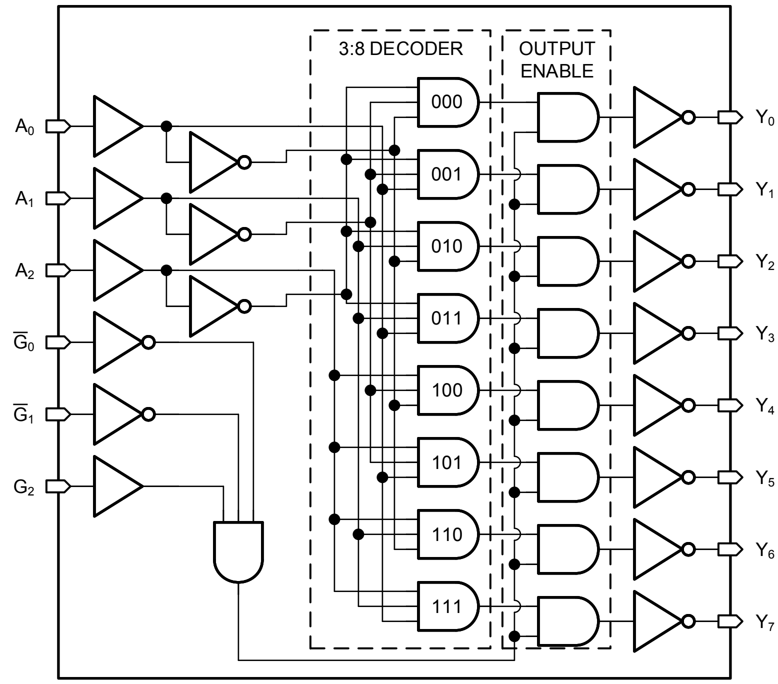
SN74LV138A-Q1 デバイスは、2V～5.5V の V_{CC} で動作するよう設計された 3 ライン対 8 ラインのデコーダ / デマルチプレクサです。

バイナリ選択入力 (A_0、A_1、A_2) と 3 つのイネーブル入力 (G2、$\overline{G0}$、$\overline{G1}$) の条件に応じて、8 つの出力ラインのいずれかを選択します。2 つのアクティブ Low ($\overline{G0}$、$\overline{G1}$) および 1 つのアクティブ High (G2) イネーブル入力により、拡張時に外部ゲートまたはインバータが不要になります。

デバイス情報

部品番号	パッケージ (1)	本体サイズ
SN74LV138A-Q1	BQB (WQFN、16)	3.60mm × 2.60mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



論理図 (正論理)

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4 Revision History

DATE	REVISION	NOTES
December 2022	*	Initial Release

5 Pin Configuration and Functions

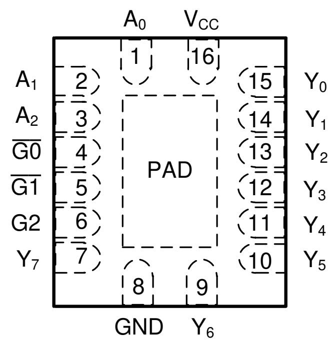


図 5-1. BQB Package 16-Pin (Top View)

表 5-1. Pin Functions

PIN		TYPE[(1)]	DESCRIPTION
NAME	NO.		
A_0	1	I	Address select 0
A_1	2	I	Address select 1
A_2	3	I	Address select 2
G2	6	I	Strobe input
$\overline{G0}$	4	I	Strobe input, active low
$\overline{G1}$	5	I	Strobe input, active low
GND	8	G	Ground
V_{CC}	16	P	Positive supply
Y_0	15	O	Output 0
Y_1	14	O	Output 1
Y_2	13	O	Output 2
Y_3	12	O	Output 3
Y_4	11	O	Output 4
Y_5	10	O	Output 5
Y_6	9	O	Output 6
Y_7	7	O	Output 7
Thermal Pad		-	Thermal Pad[(2)]

(1) Signal Types: I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power
(2) BQB package only

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) [(1)]

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	7	V
V_I	Input voltage range[(2)]		–0.5	7	V
V_O	Voltage range applied to any output in the high-impedance or power-off state[(2)]		–0.5	7	V
V_O	Output voltage range[(2) (3)]		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–20	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_{stg}	Storage temperature range		–65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2[(1)]	±2000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions[1]

			SN74LV138A-Q1 MIN	SN74LV138A-Q1 MAX	UNIT
V_{CC}	Supply voltage		2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		V
		V_{CC} = 2.3 V to 2.7 V	V_{CC} × 0.7		
		V_{CC} = 3 V to 3.6 V	V_{CC} × 0.7		
		V_{CC} = 4.5 V to 5.5 V	V_{CC} × 0.7		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5	V
		V_{CC} = 2.3 V to 2.7 V		V_{CC} × 0.3	
		V_{CC} = 3 V to 3.6 V		V_{CC} × 0.3	
		V_{CC} = 4.5 V to 5.5 V		V_{CC} × 0.3	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50	µA
		V_{CC} = 2.3 V to 2.7 V		–2	mA
		V_{CC} = 3 V to 3.6 V		–6	
		V_{CC} = 4.5 V to 5.5 V		–12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50	µA
		V_{CC} = 2.3 V to 2.7 V		2	mA
		V_{CC} = 3 V to 3.6 V		6	
		V_{CC} = 4.5 V to 5.5 V		12	
Δt/Δv	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V		200	ns/V
		V_{CC} = 3 V to 3.6 V		100	
		V_{CC} = 4.5 V to 5.5 V		20	
T_A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*.

6.4 Thermal Information

THERMAL METRIC[1]		SN74LV138A-Q1 WBQB (WQFN) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	82.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54.9	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	54.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	32.5	°C/W

(1) For more information about traditional and new thermal metrics, see *IC Package Thermal Metrics*.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	SN74LV138A-Q1			UNIT
				MIN	TYP	MAX	
V_{OH}	High-Level Output Voltage	I_{OH} = –50 µA	2 V to 5.5 V	V_{CC} – 0.1			V
		I_{OH} = –2 mA	2.3 V	2			
		I_{OH} = –6 mA	3 V	2.48			
		I_{OH} = –12 mA	4.5 V	3.8			
V_{OL}	Low-Level Output Voltage	I_{OL} = 50 µA	2 V to 5.5 V			0.1	V
		I_{OL} = 2 mA	2.3 V			0.4	
		I_{OL} = 6 mA	3 V			0.44	
		I_{OL} = 12 mA	4.5 V			0.55	
I_I	Input Current	V_I = 5.5 V or GND	0 to 5.5 V			±1	µA
I_{CC}	Supply Current	V_I = V_{CC} or GND, I_O = 0	5.5 V			20	µA
I_{off}	Input/Output Power-Off Leakage Current	V_I or V_O = 0 to 5.5 V	0			5	µA
C_i	Input Capacitance	V_I = V_{CC} or GND	3.3 V		2.1		pF

6.6 Switching Characteristics - V_{CC} = 2.5 V ± 0.25 V

over recommended operating free-air temperature range (unless otherwise noted) (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74LV138A-Q1		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	A_0, A_1, A_2	Y	C_L = 15 pF		11.7	17.6	1	21	ns
	G2				12.3	19.2	1	22	
	$\overline{G0}$ or $\overline{G1}$				11.4	18.2	1	21	
t_{pd}	A_0, A_1, A_2	Y	C_L = 50 pF		14.9	21.4	1	25	ns
	G2				15.7	22.6	1	26	
	$\overline{G0}$ or $\overline{G1}$				14.8	22	1	25	

6.7 Switching Characteristics - V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74LV138A-Q1		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	A_0, A_1, A_2	Y	C_L = 15 pF		8.1	11.4	1	13.5	ns
	G2				8.4	12.8	1	15	
	$\overline{G0}$ or $\overline{G1}$				7.8	11.4	1	13.5	
t_{pd}	A_0, A_1, A_2	Y	C_L = 50 pF		10.3	15.8	1	18	ns
	G2				10.6	16.3	1	18.5	
	$\overline{G0}$ or $\overline{G1}$				10	14.9	1	17	

6.8 Switching Characteristics - V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74LV138A-Q1		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	A_0, A_1, A_2	Y	C_L = 15 pF		5.6	8.1	1	9.5	ns
	G2				5.7	8.1	1	9.5	
	$\overline{G0}$ or $\overline{G1}$				5.4	8.1	1	9.5	
t_{pd}	A_0, A_1, A_2	Y	C_L = 50 pF		7	10.1	1	11.5	ns
	G2				7.1	10.1	1	11.5	
	$\overline{G0}$ or $\overline{G1}$				6.8	10.1	1	11.5	

6.9 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	16.8	pF
			5 V	19.1	

6.10 Typical Characteristics

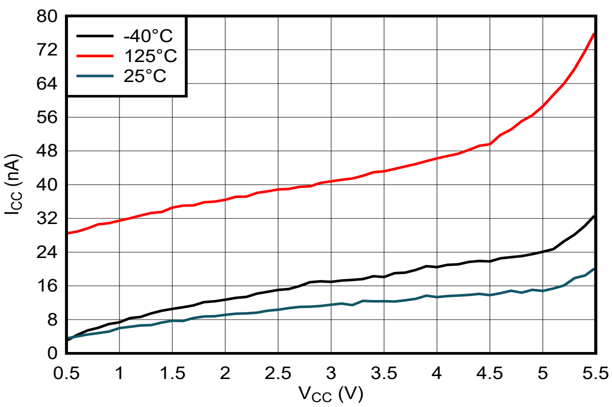


図 6-1. Supply Current (I_{CC}) vs Supply Voltage (V_{CC})

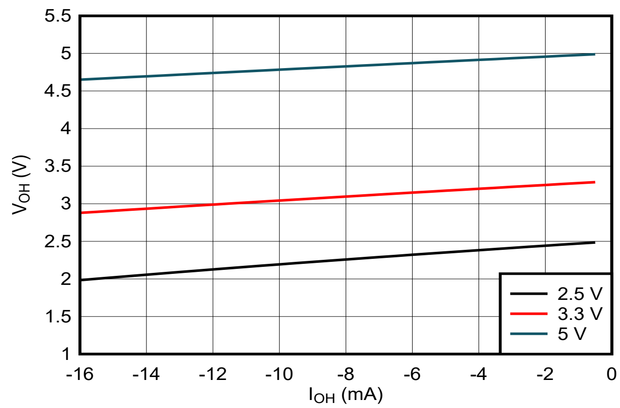


図 6-2. Output Voltage vs Current in HIGH State

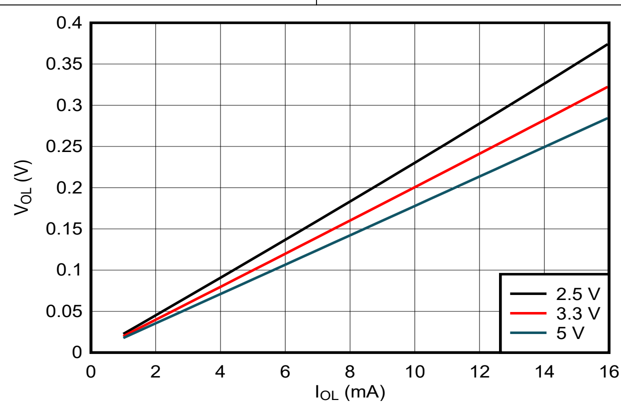
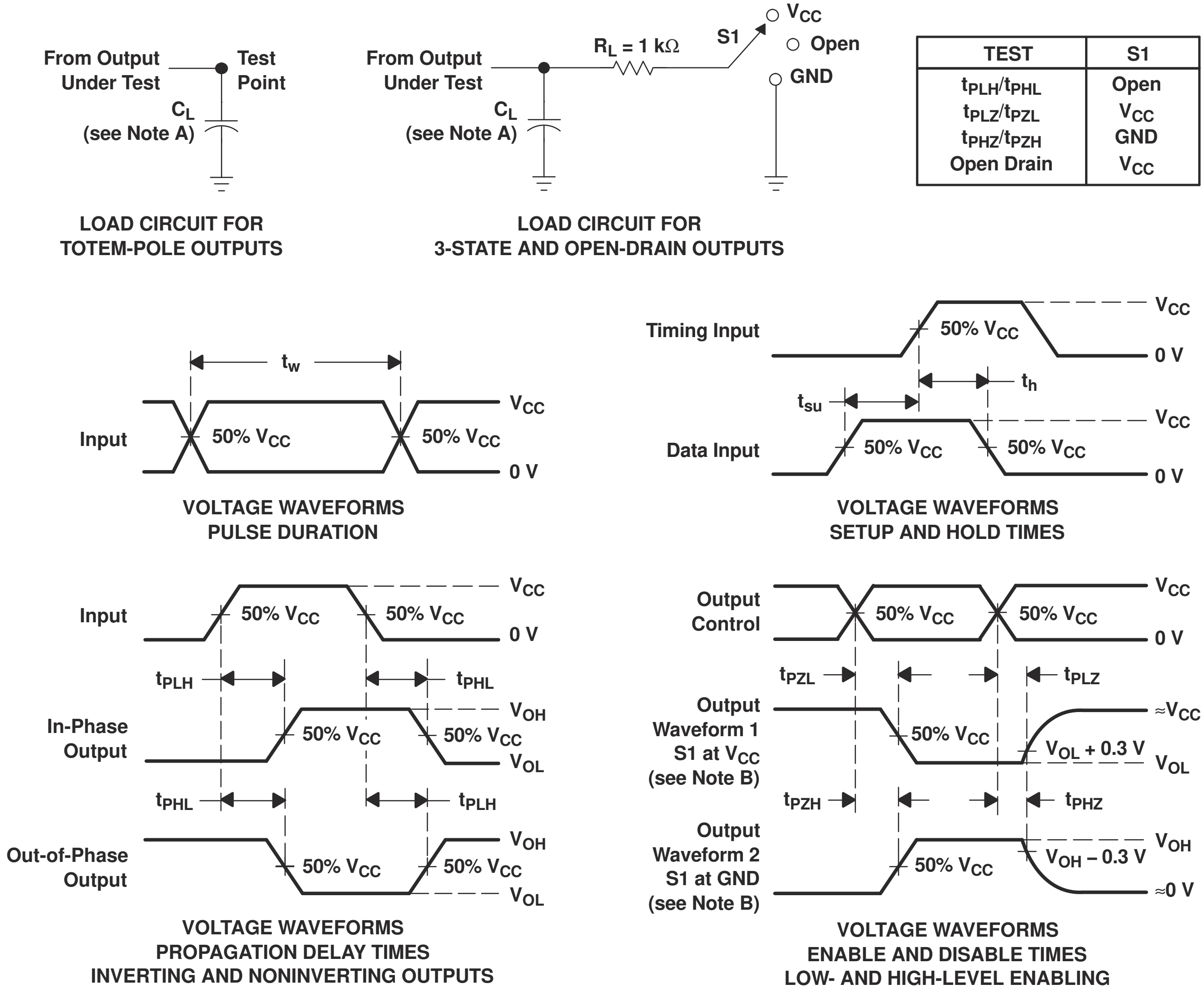


図 6-3. Output Voltage vs Current in LOW State

7 Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}

NOTES:
- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. t_{PHL} and t_{PLH} are the same as t_{pd}.
- H. All parameters and waveforms are not applicable to all devices.

図 7-1. Load Circuits and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LV138A-Q1 devices are 3-line to 8-line decoders/demultiplexers designed for 2 V to 5.5 V V_{CC} operation.

These devices are designed for high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, these decoders can be used to minimize the effects of system decoding. When employed with high-speed memories utilizing a fast enable circuit, the delay times of these decoders and the enable time of the memory usually are less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

The conditions at the binary-select inputs (A_0, A_1, A_2) and the three enable inputs (G2, $\overline{G0}$, $\overline{G1}$) select one of eight output lines. The two active-low ($\overline{G0}$, $\overline{G1}$) and one active-high (G2) enable inputs reduce the need for external gates or inverters when expanding. A 24-line decoder can be implemented without external inverters and a 32-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

These devices are fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

8.2 Functional Block Diagram

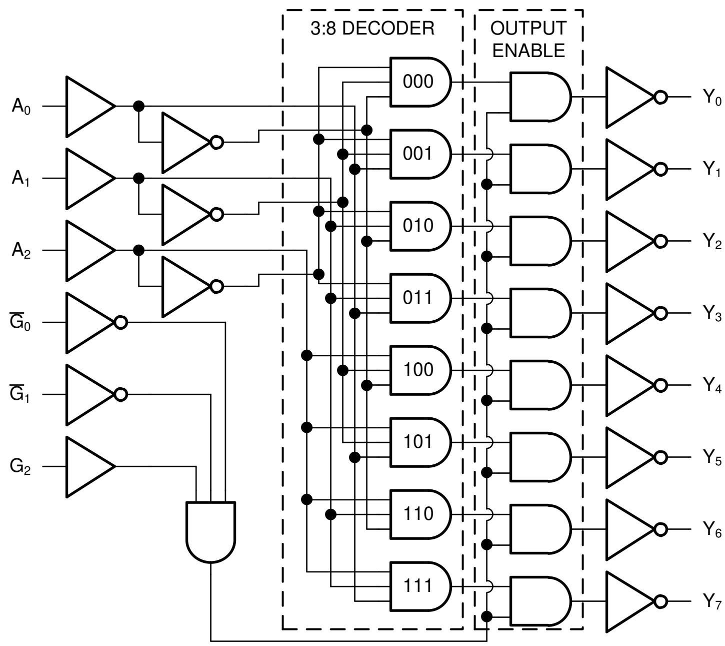


図 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

8.3.1 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a 10-kΩ resistor, however, is recommended and will typically meet all requirements.

8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.3 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

8.3.4 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet for which packages include this feature.

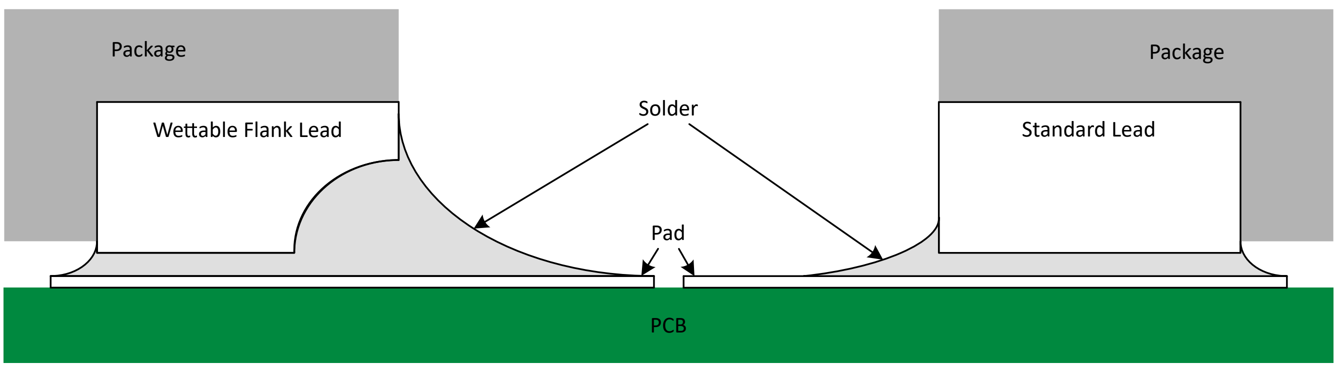


図 8-2. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in 図 8-2, a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

8.3.5 Clamp Diode Structure

図 8-3 shows the inputs and outputs to this device have negative clamping diodes only.

> 注意
> Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

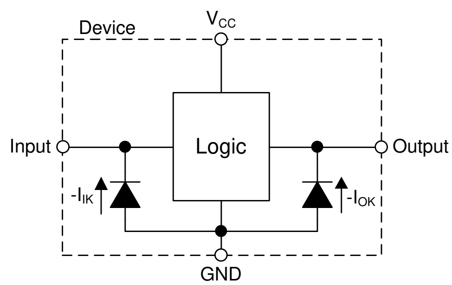


図 8-3. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Function Table

ENABLE INPUTS(1)			SELECT INPUTS			OUTPUTS(2)							
G2	$\overline{G0}$	$\overline{G1}$	A_2	A_1	A_0	Y0	Y1	Y20	Y3	Y4	Y5	Y6	Y7
X	H	X	X	X	X	H	H	H	H	H	H	H	H
X	X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
(2) H = Driving High, L = Driving Low, Z = High Impedance State

9 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Application Information

The SN74LV138A-Q1 is a low drive CMOS device that can be used for a multitude of output expansion applications where output ringing is a concern. The low-drive and slow-edge rates minimize overshoot and undershoot on the outputs.

9.2 Typical Application

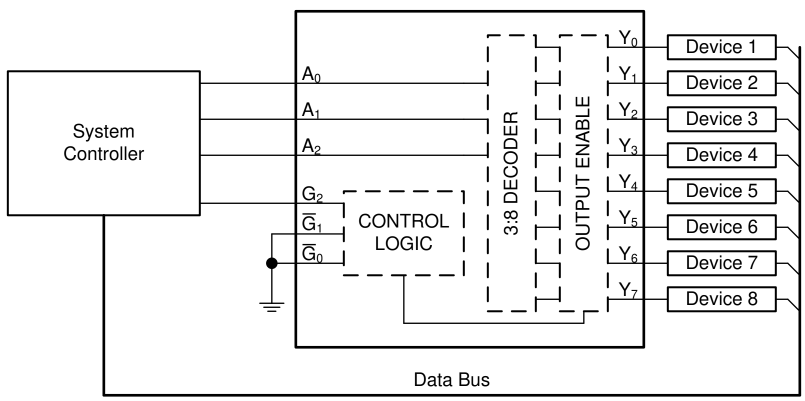


図 9-1. Output Exapnsion with Multiplexer

9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV138A-Q1 plus the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV138A-Q1 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV138A-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV138A-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*.

> 注意
> The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV138A-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-kΩ resistor value is often used due to these factors.

The SN74LV138A-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.4 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV138A-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

9.2.5 Application Curves

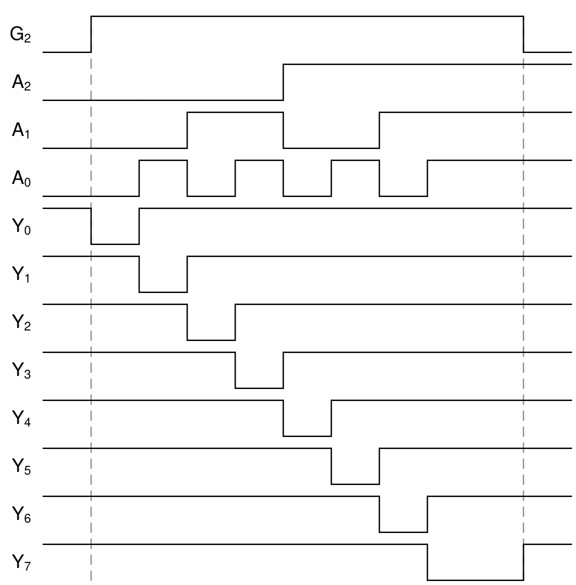


図 9-2. Application Timing Diagram

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Absolute Maximum Ratings* section. Each V_{CC} terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1-μF capacitor; if there are multiple V_{CC} terminals, then TI recommends a 0.01-μF or 0.022-μF capacitor for each power terminal. Multiple bypass capacitors can be paralleled to reject different frequencies of noise. Frequencies of 0.1 μF and 1 μF are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

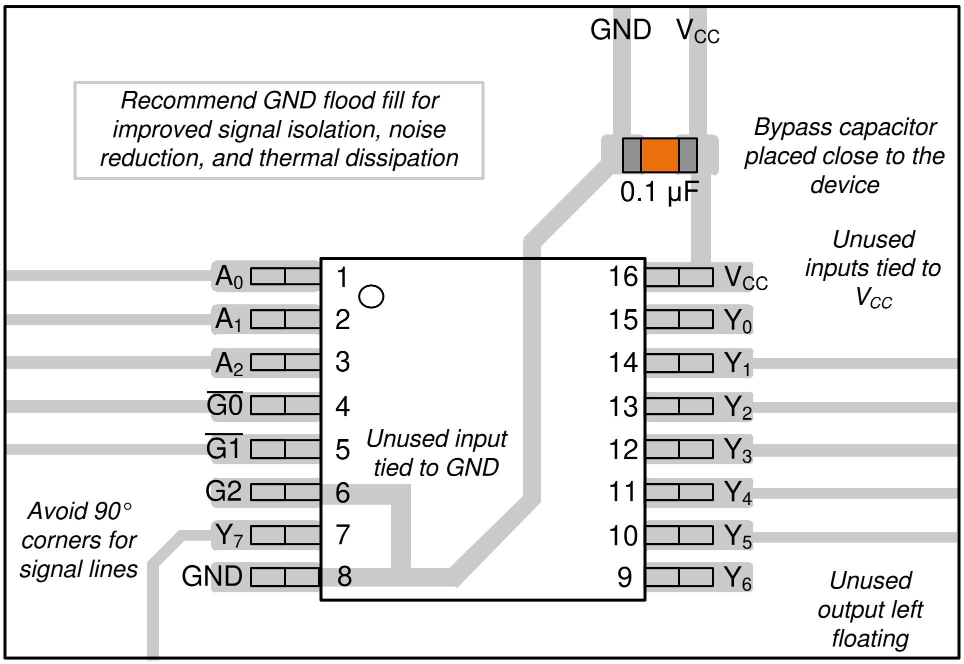


図 11-1. Layout Example for the SN74LV138A-Q1

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

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12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.
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12.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74LV138AQWBQBRQ1	Active	Production	WQFN (BQB) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV138Q
SN74LV138AQWBQBRQ1.A	Active	Production	WQFN (BQB) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV138Q

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LV138A-Q1 :

- Catalog : SN74LV138A

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

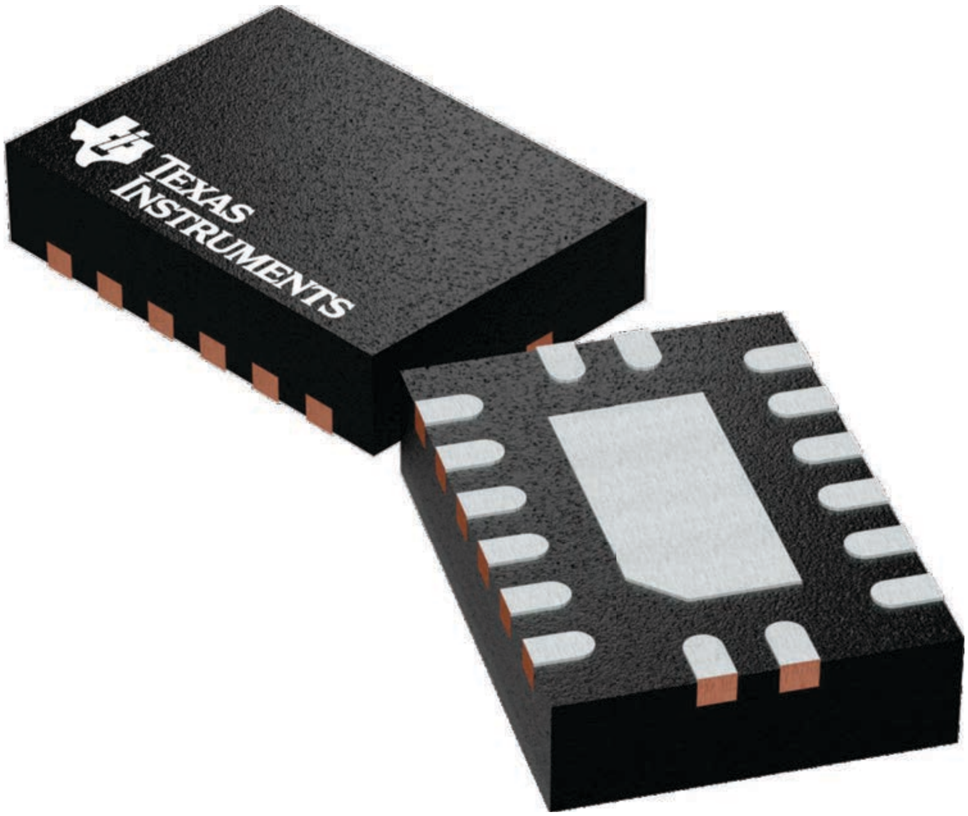
BQB 16

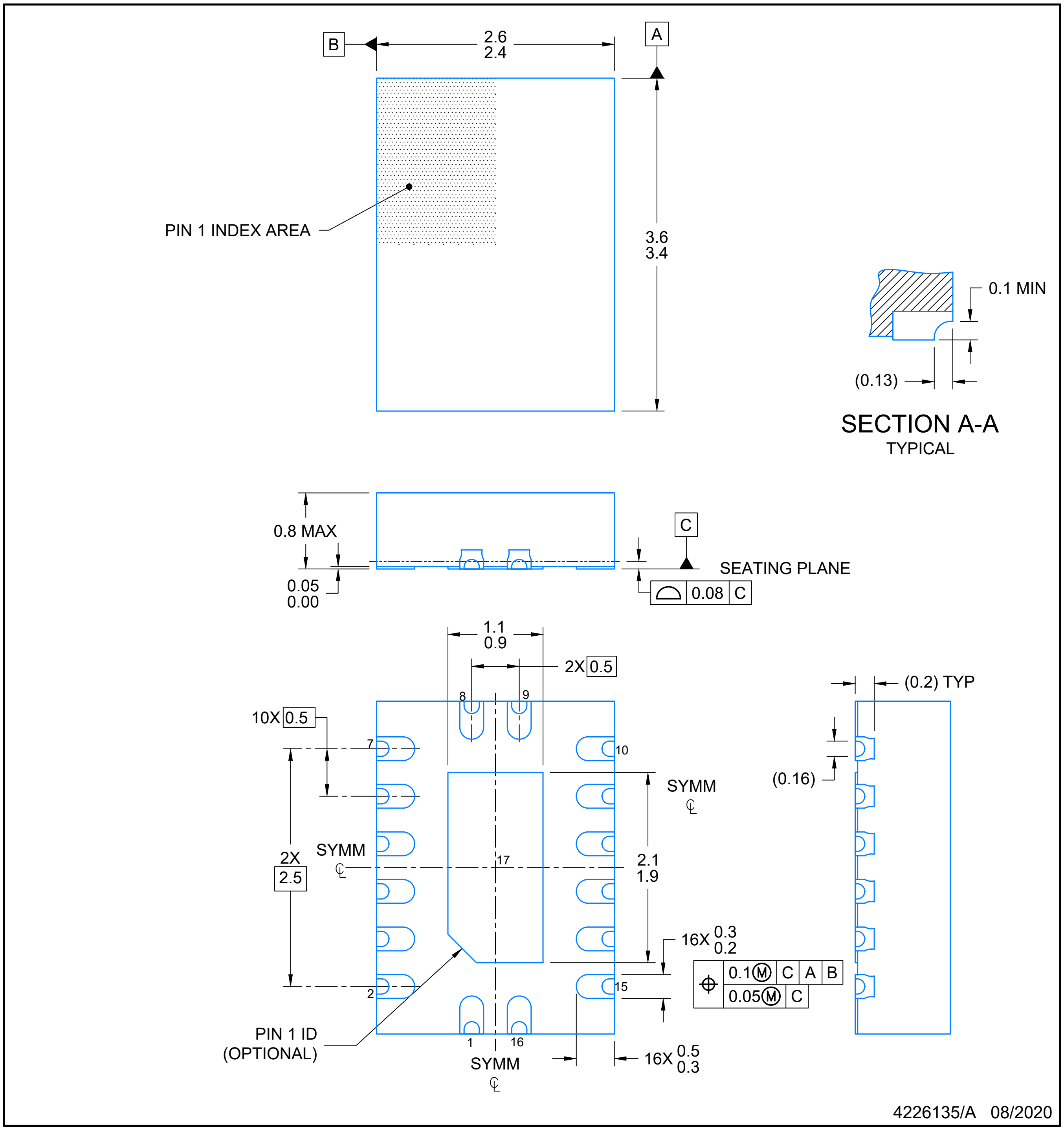
WQFN - 0.8 mm max height

2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

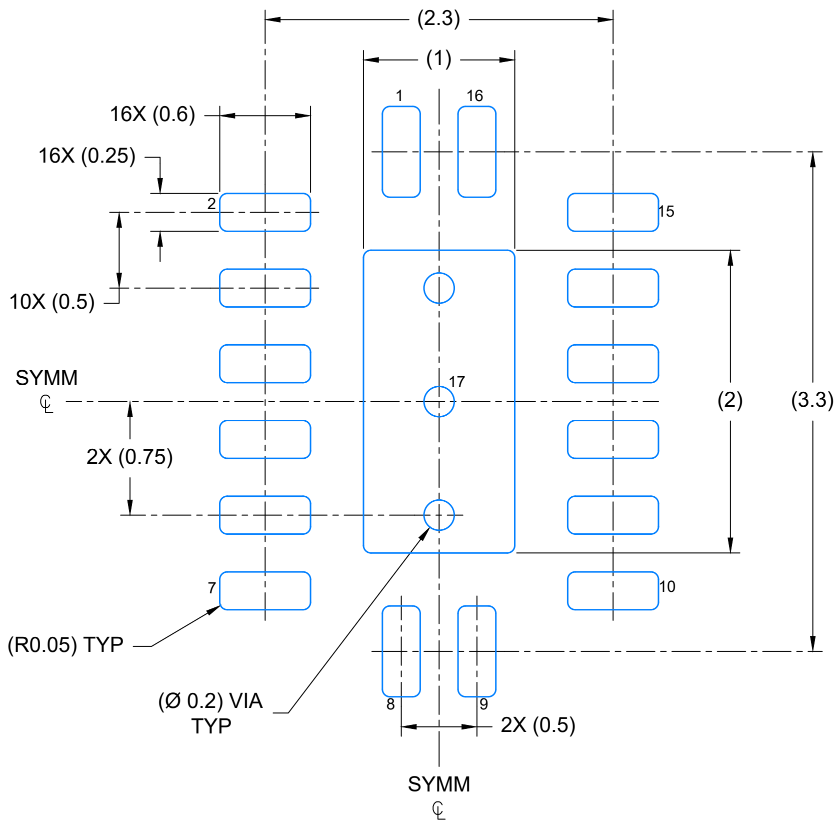




NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

INDSTNAME



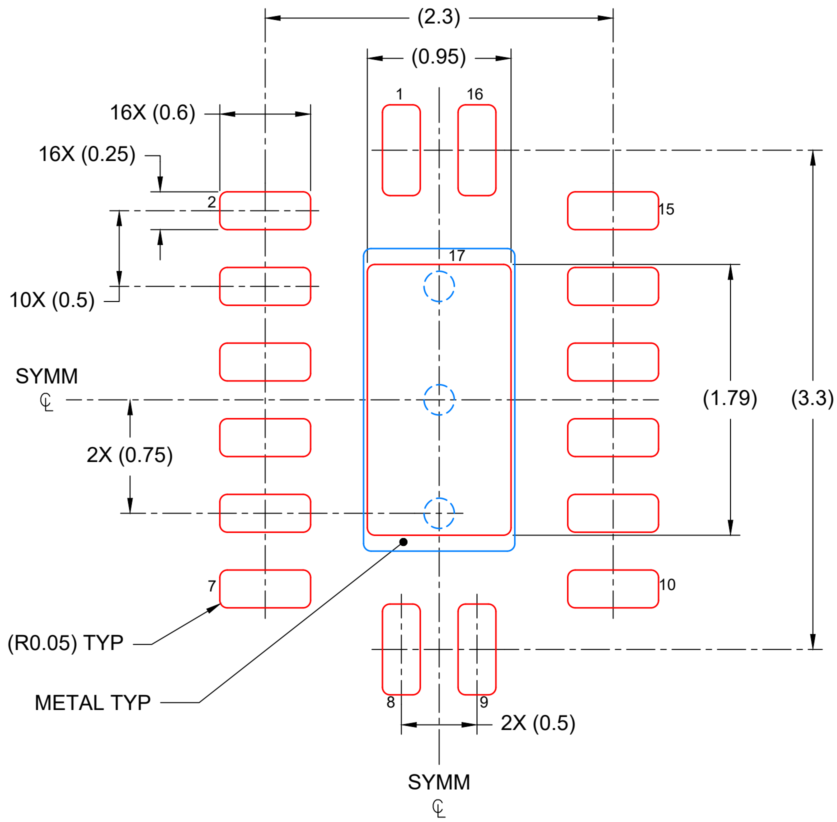
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

INDSTNAME



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.